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INFORMATION DISCLOSURE
STATEMENT BY APPLICANY
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Filing Date
First Named Inventor
Group Art Unit

Examiner Name

Attorney Docket No: 303.620US2

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Substitute for form 1449A/PTO	Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.  Complete If Known		
INFORMATION DISCLOSURE	Application Number	10/719217	
STATEMENT BY APP HOARTE (Use as many sheets as necessar)	Filing Date	November 20, 2003	
JUN 0 1 2004 &	First Named Inventor	Forbes, Leonard	
	Group Art Unit	2824	
	Examiner Name	Nguyen, Hien	
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